

# High Voltage Switching Diode, 250 V

## BAS21TMR6

The BAS21TMR6T1G device houses three high-voltage switching diodes in a SC-74 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

### Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (EACH DIODE)

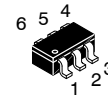
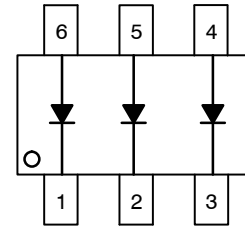
Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	250	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	311 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	402	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	347 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	360	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

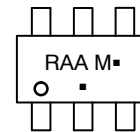
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ 10 mm<sup>2</sup>, 2 oz copper traces
2. FR-4 @ 25 mm<sup>2</sup>, 2 oz copper traces



SC-74  
CASE 318F

### MARKING DIAGRAM



- RAA = Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BAS21TMR6T1G	SC-74 (Pb-Free)	3000 / Tape & Reel
NSVBAS21TMR6T1G	SC-74 (Pb-Free)	3000 / Tape & Reel
NSVBAS21TMR6T2G	SC-74 (Pb-Free)	3000 / Tape & Reel

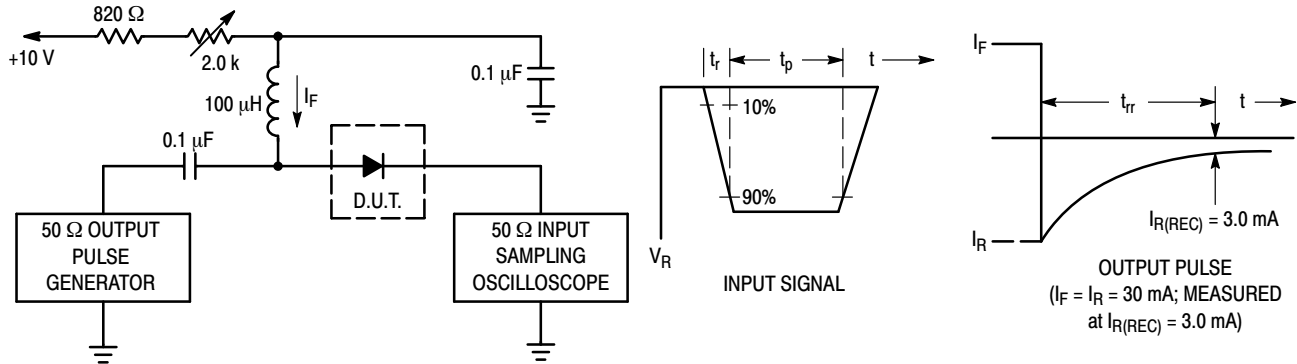
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

# BAS21TMR6

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current ( $V_R = 200\text{ Vdc}$ ) ( $V_R = 200\text{ Vdc}$ , $T_J = 150^\circ\text{C}$ )	$I_R$	-	0.1 100	$\mu\text{A}$ $\text{dc}$
Reverse Breakdown Voltage ( $I_{BR} = 100\ \mu\text{A}$ )	$V_{(BR)}$	250	-	Vdc
Forward Voltage ( $I_F = 100\ \text{mA}$ ) ( $I_F = 200\ \text{mA}$ )	$V_F$	-	1.0 1.25	Vdc
Diode Capacitance ( $V_R = 0$ , $f = 1.0\ \text{MHz}$ )	$C_D$	-	5.0	pF
Reverse Recovery Time ( $I_F = I_R = 30\ \text{mA}$ , $I_{R(REC)} = 3.0\ \text{mA}$ , $R_L = 100$ )	$t_{rr}$	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 30 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 30 mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

# BAS21TMR6

## TYPICAL CHARACTERISTICS

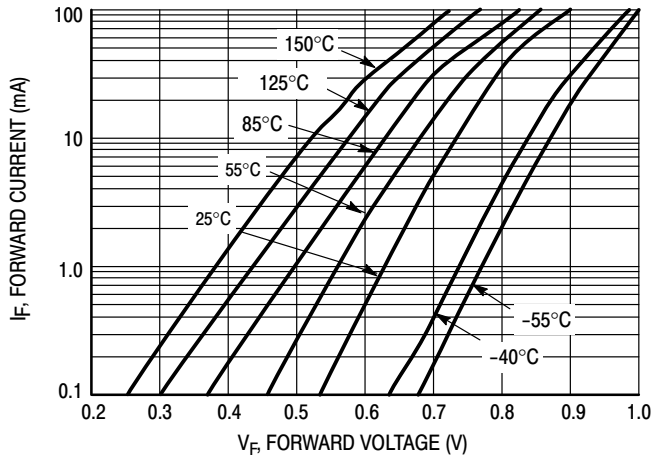


Figure 2.  $V_F$  vs.  $I_F$

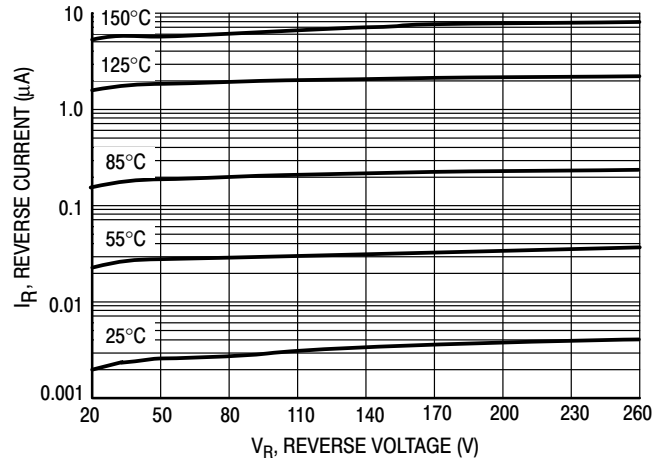


Figure 3.  $I_R$  vs.  $V_R$

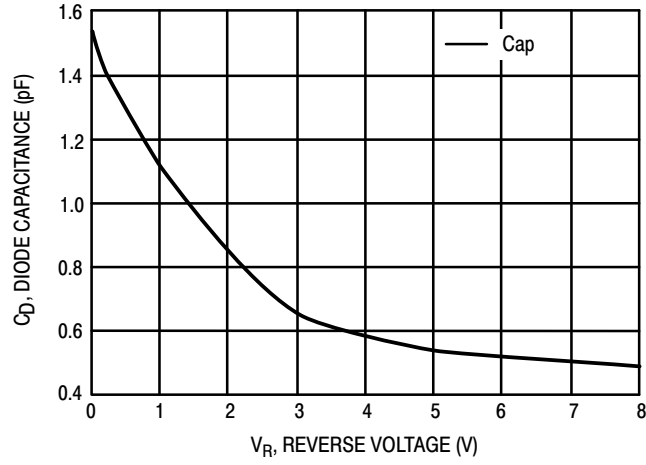


Figure 4. Capacitance

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 2:1

**SC-74**  
CASE 318F  
ISSUE P

DATE 07 OCT 2021



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
HE	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0*	---	10*	0*	---	10*

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

**SOLDERING FOOTPRINT**

- |  |   |  |   |  |  |
|--|---|--|---|--|--|
| <p><b>STYLE 1:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. ANODE<br/>6. CATHODE</p>     | <p><b>STYLE 2:</b><br/>PIN 1. NO CONNECTION<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. NO CONNECTION<br/>5. COLLECTOR<br/>6. BASE</p> | <p><b>STYLE 3:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 1<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 2<br/>6. COLLECTOR 1</p> | <p><b>STYLE 4:</b><br/>PIN 1. COLLECTOR 2<br/>2. EMITTER 1/EMITTER 2<br/>3. COLLECTOR 1<br/>4. EMITTER 3<br/>5. BASE 1/BASE 2/COLLECTOR 3<br/>6. BASE 3</p> | <p><b>STYLE 5:</b><br/>PIN 1. CHANNEL 1<br/>2. ANODE<br/>3. CHANNEL 2<br/>4. CHANNEL 3<br/>5. CATHODE<br/>6. CHANNEL 4</p> | <p><b>STYLE 6:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE</p> |
| <p><b>STYLE 7:</b><br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. DRAIN 2<br/>4. SOURCE 2<br/>5. GATE 2<br/>6. DRAIN 1</p> | <p><b>STYLE 8:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 2<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 1<br/>6. COLLECTOR 1</p>    | <p><b>STYLE 9:</b><br/>PIN 1. EMITTER 2<br/>2. BASE 2<br/>3. COLLECTOR 1<br/>4. EMITTER 1<br/>5. BASE 1<br/>6. COLLECTOR 2</p> | <p><b>STYLE 10:</b><br/>PIN 1. ANODE/CATHODE<br/>2. BASE<br/>3. EMITTER<br/>4. COLLECTOR<br/>5. ANODE<br/>6. CATHODE</p>                                    | <p><b>STYLE 11:</b><br/>PIN 1. EMITTER<br/>2. BASE<br/>3. ANODE/CATHODE<br/>4. ANODE<br/>5. CATHODE<br/>6. COLLECTOR</p>   |  |

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<b>DESCRIPTION:</b>	<b>SC-74</b>	<b>PAGE 1 OF 1</b>

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